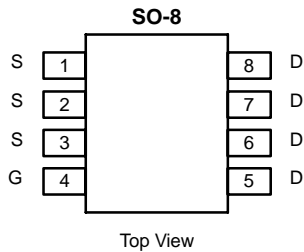




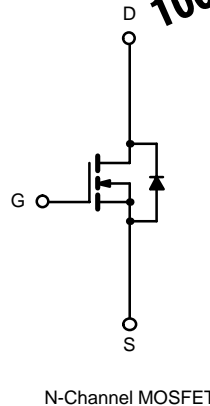
## N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
20	0.005 @ V <sub>GS</sub> = 4.5 V	21
	0.0075 @ V <sub>GS</sub> = 2.5 V	17

**TrenchFET<sup>®</sup>**  
Power MOSFETs  
2.5-V Rated  
100% R<sub>G</sub> Tested



Ordering Information: Si4876DY  
Si4876DY-T1 (with Tape and Reel)



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	20		V
Gate-Source Voltage		V <sub>GS</sub>	± 12		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	21	14	A
	T <sub>A</sub> = 85 °C		15	10	
Pulsed Drain Current		I <sub>DM</sub>	50		
Avalanche Current		I <sub>AS</sub>	42		
Single Avalanche Energy		E <sub>AS</sub>	88		mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	3	1.3	mS
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.6	1.6	W
	T <sub>A</sub> = 85 °C		1.9	0.8	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 sec	R <sub>thJA</sub>	29	35	°C/W
	Steady State		67	80	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	13	16	

Notes  
a. Surface Mounted on 1" x 1" FR4 Board.

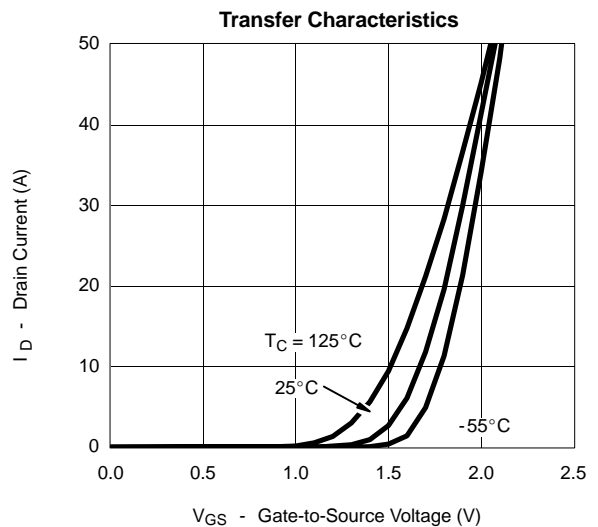
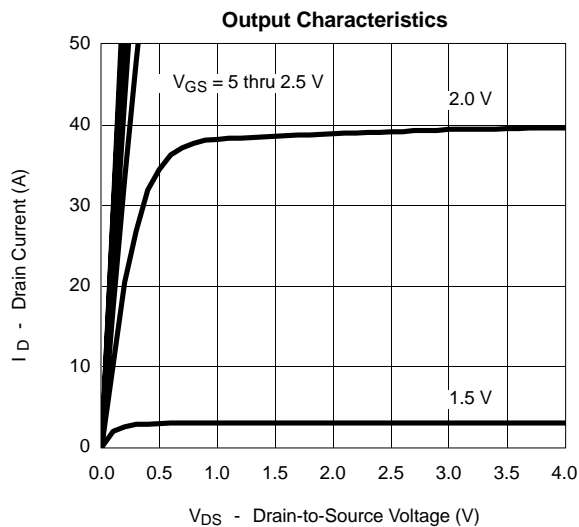


SPECIFICATIONS (T <sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.6			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			20	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 4.5 V	50			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 21 A		0.0037	0.005	Ω
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 17 A		0.0058	0.0075	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 21 A		17		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 3 A, V <sub>GS</sub> = 0 V		0.8	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 21 A		55	80	nC
Gate-Source Charge	Q <sub>gs</sub>			13		
Gate-Drain Charge	Q <sub>gd</sub>			11		
Gate Resistance	R <sub>g</sub>		2.0	2.7	4.6	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10 V, R <sub>L</sub> = 10 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		40	60	ns
Rise Time	t <sub>r</sub>			30	45	
Turn-Off Delay Time	t <sub>d(off)</sub>			175	260	
Fall Time	t <sub>f</sub>			70	105	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 3 A, di/dt = 100 A/μs		56	85	

**Notes**

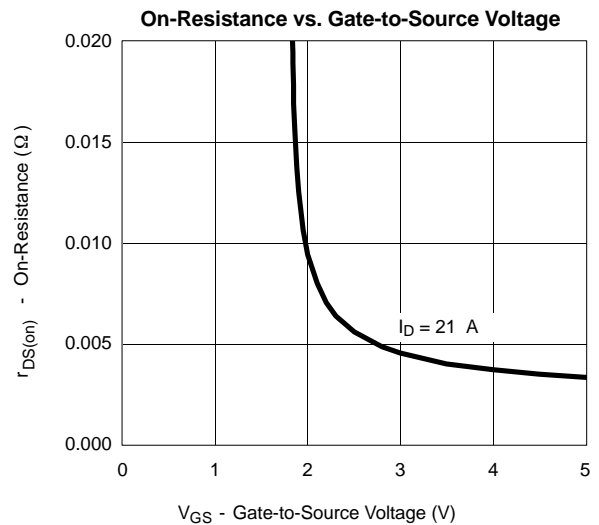
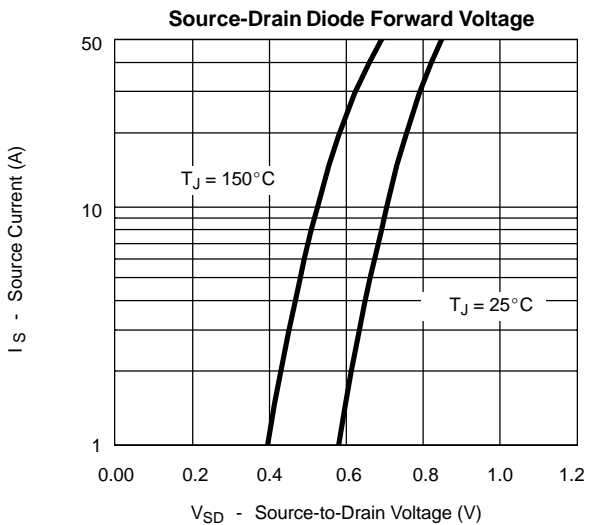
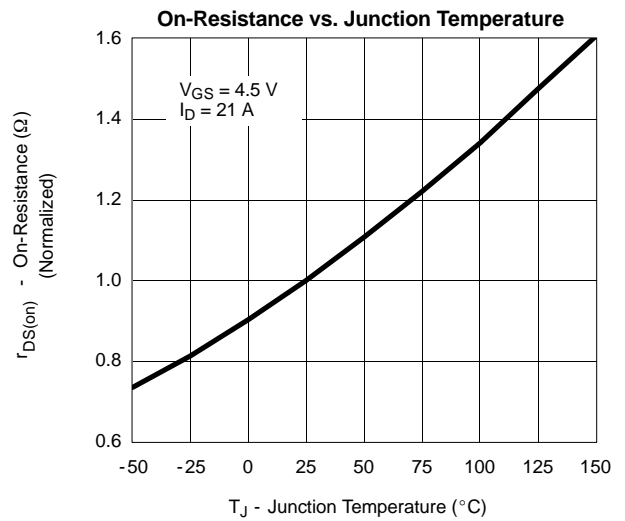
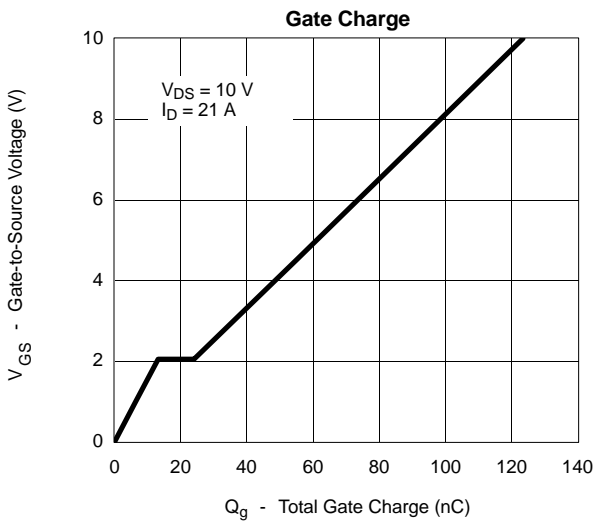
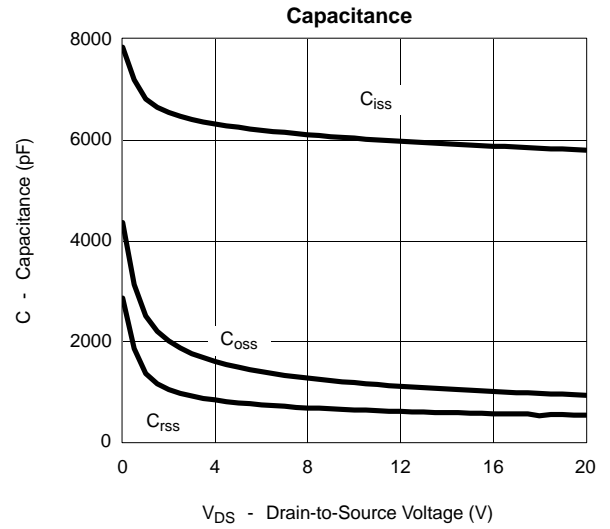
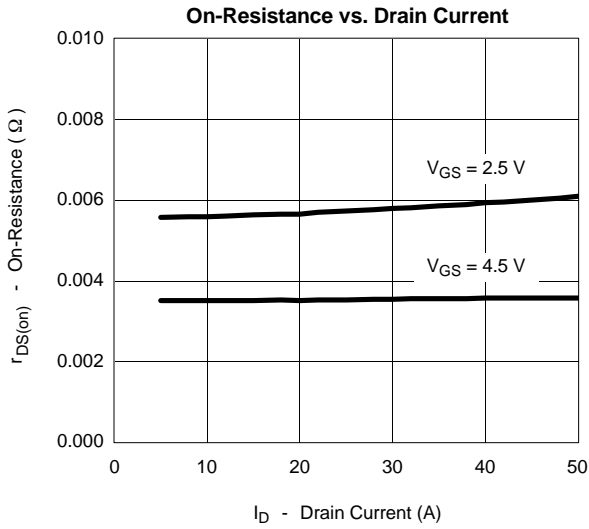
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

### TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

